Next Gen CMP Challenges in 3D Memory Architectures

F4 CMP Team, Micron Technology SEMICON WEST 2018, NCCAVS Users Group

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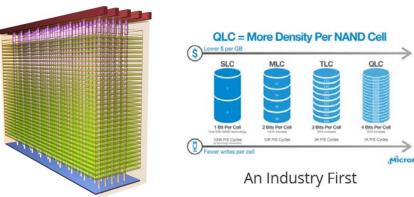


Micron Technology: 40 Years...

...and we believe strongly in the future

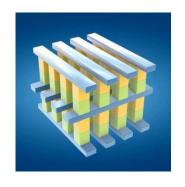
Non-Volatile Technology Announcements

3D NAND & QLC



QLC: Lower TCO, More Capacity & Smaller Footprint

3D XPoint™ & QUANTX





QUANTX: 10x better performance than NAND SSDs



CMP Evolution for 3D Memory Architectures

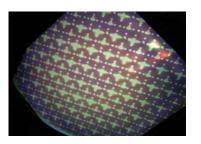
Evolutionary Challenges require Revolutionary Solutions **Next Gen 3D Architectures** - FOAK Material polish - x-Wafer Non-uniformity **3D XP Introduction** - Local Planarization - FOAK Material Polish - Endpoint & Process Control - x-Wafer Non-uniformity - Defectivity - Local Planarization - Cost Reduction - Endpoint & Process control - Time-to-Solution (TTS) 2D-3D NAND Transition - FOAK Material Polish - x-Wafer Non-uniformity - Local Planarization - Defectivity

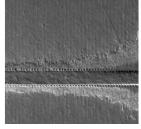


FOAK Material Polish

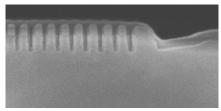
Versatile FOAK Materials driven by

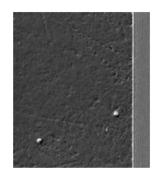
- High Aspect ratio Gap fill
- Large Area Gap fill
- Mechanical Integrity Requirements
- Variable Dielectric constants
- Exotic materials for Pillar etch

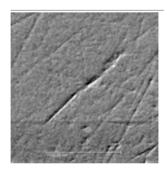


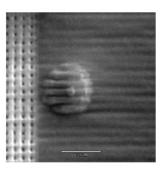


EOA Erosion in high lbf regime









Increased defectivity w. Low modulus film

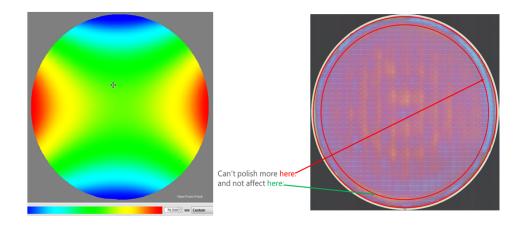
- Proactive FOAK Material polish R&D
- Extreme Mechanical polish regimes
- Faster Time-to-solution (TTS)
- Cost Effectiveness
- Continuous Improvement plan



x-Wafer Non-uniformity

High x-Wafer Non-uniformity driven by

- Stress Impacts due to 3D stack films
- Head Design limitations
- Edge Tunability
- Asymmetry Management





x-Wafer Asymmetry

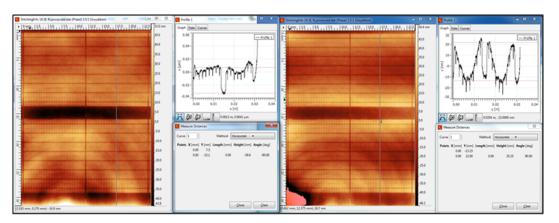
- Multi-Zone Heads
- Stress Impact Management
- Consumable parameter study
- Asymmetry Management



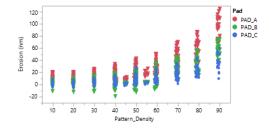
Local Planarization

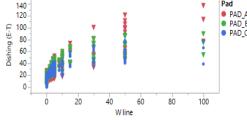
Worse Local Planarization driven by

- Local/Frame-level Stress
- Consumable compatibility
- Slurry selectivity tuning
- Variable pattern densities



Chucked Unchucked





$$Erosion = a + b * e^{c*PD}$$

Dishing =
$$\frac{c}{(1 + e^{-a*(Wline-b)})}$$

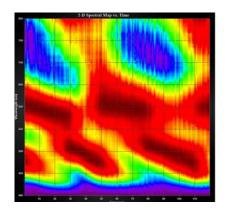
- Bulk Vs. Local Stress Modeling & Handling
- Pad & Slurry options for Planarization
- Consumable parameter study
- Proactive Pattern Density Studies



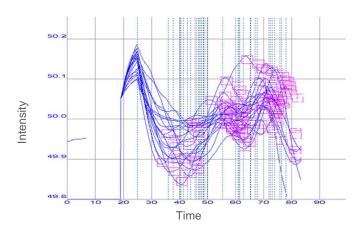
Endpoint & Process Control

Higher Process variability driven by

- Incoming Module/stress variability
- Process/Consumable variability
- Friction Endpoint regime fail (S/N)
- Ineffective/Insufficient Metrology



Redundant spectral signature issue with White Light



Final platen EP variability due to prior platen non-uniformity

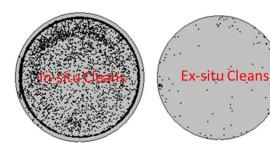
- Insitu Zonal Endpoint Detection & Control
- Insitu Metrology and Process control
- Big Data Solutions to extract & Correlate spectral info
- Cost effectiveness



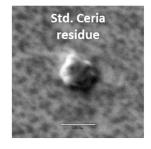
Defectivity

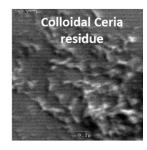
High Defectivity driven by

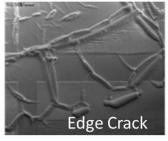
- Complexity in maintaining Reg E/Bevel health
- Process Scratch/particle defectivity
- Film Quality Versus Polish consumables
- Incoming/Equipment contamination

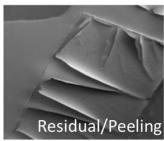


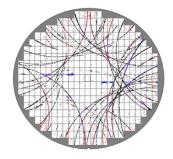












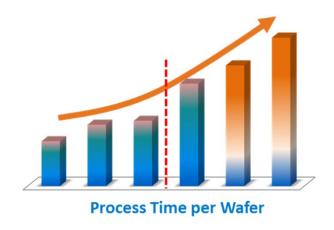
- Low Defectivity Consumable combinations
- Edge tunability/Bevel roll-off improvements
- Enhanced Insitu Cleans performance
- Low TCO/High Through-put Buff platform

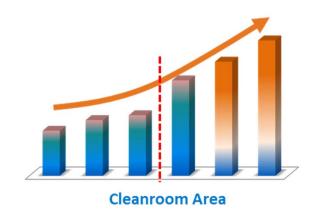


Cost Reduction & Faster TTS

Cost effective & Faster TTS opportunities

- Enhanced Process capability
- Long-term Roadmap sharing
- Cost effective TTS



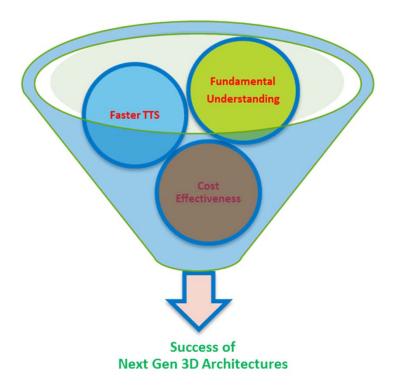


- Faster, Capable & Flexible platforms
- Faster & Capable consumables
- Insitu Process Metrology & Characterization
- Lookahead Roadmap Solutions Development
- Pursuit of continuous improvement



Summary

- Transition to 3D architectures (NAND, XP) presented complex CMP challenges over past few years.
- Next-gen 3D technodes present even more stringent requirements for FOAK Material polish, WIW and WID NU, process control, defectivity and cost reduction.
- Fundamental understanding of problem statement and root cause, combined with latest scientific opportunities such as AI and advanced Big Data analytics will foster innovative CMP technology solutions such as statistical modeling of consumables and insitu process control.
- Long term Vendor Partnerships are key to identifying these advanced cost effective solutions with excellent TTS.





Questions?



